

## Standard Recovery Diodes (Stud Version), 25 A



DO-203AA (DO-4)

**FEATURES**

- High surge current capability
- Stud cathode and stud anode version
- Wide current range
- Types up to 1200 V  $V_{RRM}$
- RoHS compliant


**RoHS**  
COMPLIANT

**TYPICAL APPLICATIONS**

- Battery charges
- Converters
- Power supplies
- Machine tool controls

**PRODUCT SUMMARY**

$I_{F(AV)}$	25 A
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**MAJOR RATINGS AND CHARACTERISTICS**

PARAMETER	TEST CONDITIONS	VALUES	UNITS
$I_{F(AV)}$		25	A
	$T_C$	120	°C
$I_{F(RMS)}$		40	A
$I_{FSM}$	50 Hz	356	A
	60 Hz	373	
$I^2t$	50 Hz	636	A <sup>2</sup> s
	60 Hz	580	
$V_{RRM}$	Range	100 to 1200	V
$T_J$		- 65 to 175	°C

**ELECTRICAL SPECIFICATIONS**
**VOLTAGE RATINGS**

TYPE NUMBER	VOLTAGE CODE	$V_{RRM}$ , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	$V_{RSM}$ , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	$V_{R(BR)}$ , MINIMUM AVALANCHE VOLTAGE V (1)	$I_{RRM}$ MAXIMUM AT $T_J = 175$ °C mA
25F(R)	10	100	150	-	12
	20	200	275	-	
	40	400	500	500	
	60	600	725	750	
	80	800	950	950	
	100	1000	1200	1150	
	120	1200	1400	1350	

**Note**

 (1) Avalanche version only available from  $V_{RRM}$  400 V to 1200 V

FORWARD CONDUCTION					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum average forward current at case temperature	$I_{F(AV)}$	180° conduction, half sine wave		25	A
				120	°C
Maximum RMS forward current	$I_{F(RMS)}$			40	A
Maximum on-repetitive peak reverse power	$P_R^{(1)}$	10 $\mu$ s square pulse, $T_J = T_J$ maximum		10	K/W
Maximum peak, one-cycle forward, non-repetitive surge current	$I_{FSM}$	t = 10 ms	No voltage reappplied	356	A
		t = 8.3 ms		373	
		t = 10 ms	100 % $V_{RRM}$ reappplied	300	
		t = 8.3 ms		314	
Maximum $I^2t$ for fusing	$I^2t$	t = 10 ms	No voltage reappplied	636	A <sup>2</sup> s
		t = 8.3 ms		580	
		t = 10 ms	100 % $V_{RRM}$ reappplied	450	
		t = 8.3 ms		410	
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	t = 0.1 to 10 ms, no voltage reappplied		6360	A <sup>2</sup> $\sqrt{s}$
Low level value of threshold voltage	$V_{F(TO)1}$	$(16.7\% \times \pi \times I_{F(AV)} < I < \pi \times I_{F(AV)})$ , $T_J = T_J$ maximum		0.80	V
High level value of threshold voltage	$V_{F(TO)2}$	$(I > \pi \times I_{F(AV)})$ , $T_J = T_J$ maximum		0.90	
Low level value of forward slope resistance	$r_{f1}$	$(16.7\% \times \pi \times I_{F(AV)} < I < \pi \times I_{F(AV)})$ , $T_J = T_J$ maximum		6.80	m $\Omega$
High level value of forward slope resistance	$r_{f2}$	$(I > \pi \times I_{F(AV)})$ , $T_J = T_J$ maximum		5.70	
Maximum forward voltage drop	$V_{FM}$	$I_{pk} = 78$ A, $T_J = 25$ °C, $t_p = 400$ $\mu$ s rectangular wave		1.30	V

### Note

(1) Available only for avalanche version, all other parameters the same as 25F

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum junction operating temperature range	$T_J$			- 65 to 175	°C
Maximum storage temperature range	$T_{Stg}$			- 65 to 200	
Maximum thermal resistance, junction to case	$R_{thJC}$	DC operation		1.5	K/W
Maximum thermal resistance, case to heatsink	$R_{thCS}$	Mounting surface, smooth, flat and greased		0.5	
Allowable mounting torque		Not lubricated threads		1.5 + 0 - 10 % (13)	N · m (lbf · in)
		Lubricated threads		1.2 + 0 - 10 % (10)	N · m (lbf · in)
Approximate weight				7	g
				0.25	oz.
Case style		See dimensions - link at the end of datasheet		DO-203AA (DO-4)	



$\Delta R_{thJC}$ CONDUCTION				
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS
180°	0.28	0.24	T <sub>J</sub> = T <sub>J</sub> maximum	K/W
120°	0.39	0.41		
90°	0.50	0.54		
60°	0.73	0.75		
30°	1.20	1.21		

**Note**

- The table above shows the increment of thermal resistance R<sub>thJC</sub> when devices operate at different conduction angles than DC

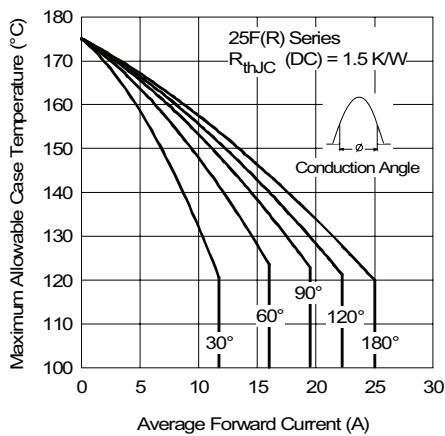


Fig. 1 - Current Ratings Characteristics

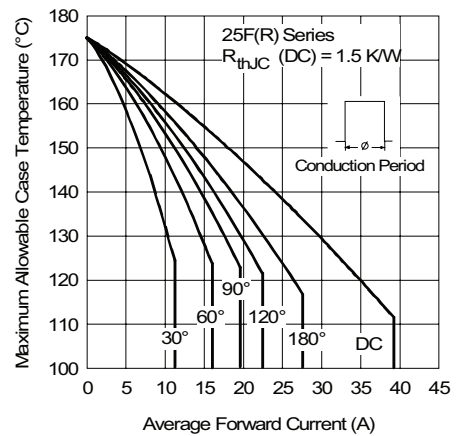


Fig. 2 - Current Ratings Characteristics

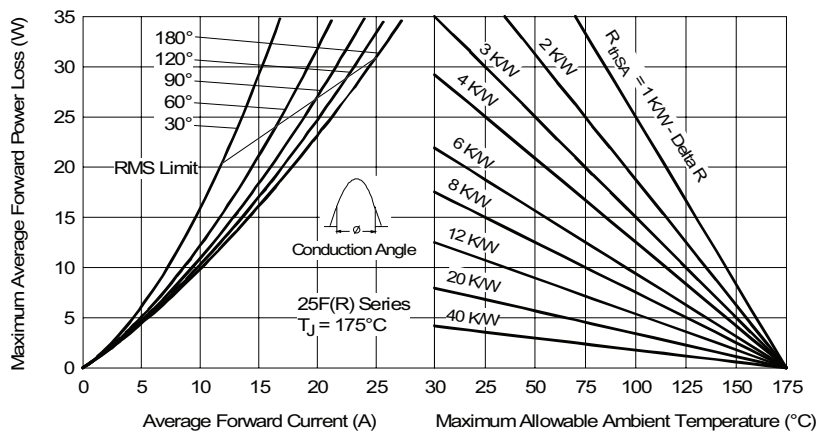


Fig. 3 - Forward Power Loss Characteristics

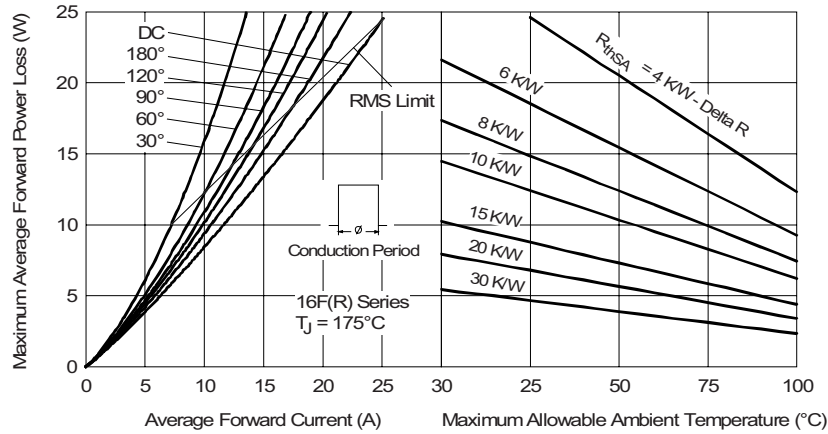


Fig. 4 - Forward Power Loss Characteristics

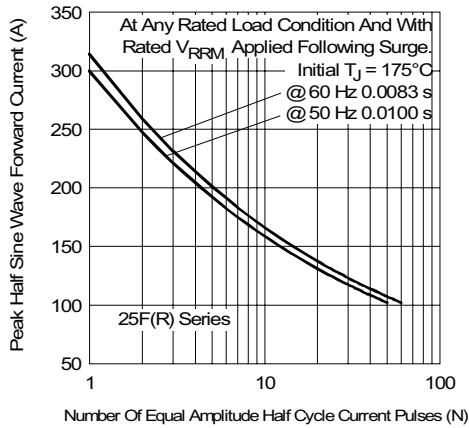


Fig. 5 - Maximum Non-Repetitive Surge Current

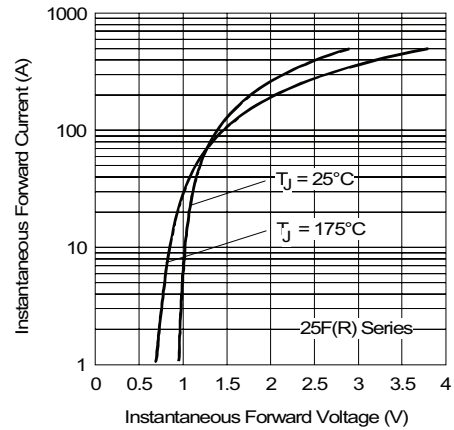


Fig. 7 - Forward Voltage Drop Characteristics

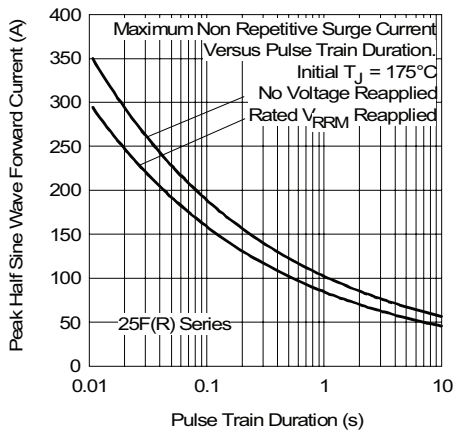


Fig. 6 - Maximum Non-Repetitive Surge Current

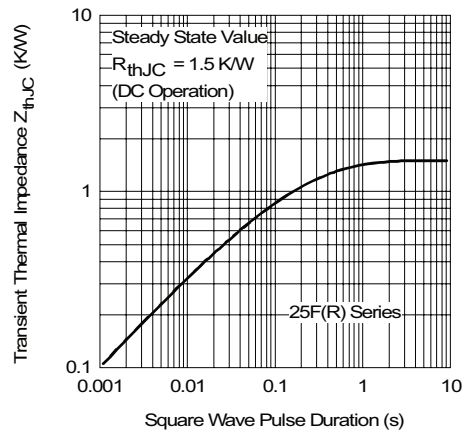
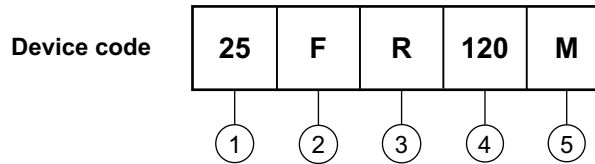


Fig. 8 - Thermal Impedance  $Z_{thJC}$  Characteristics



## ORDERING INFORMATION TABLE



- 1** - Current rating: Code =  $I_{F(AV)}$
- 2** - F = Standard device
- 3** - None = Stud normal polarity (cathode to stud)  
R = Stud reverse polarity (anode to stud)
- 4** - Voltage code x 10 =  $V_{RRM}$  (see Voltage Ratings table)
- 5** - None = Stud base DO-203AA (DO-4) 10-32UNF-2A  
M = Stud base DO-203AA (DO-4) M5 X 0.8  
(not available for avalanche diodes)

LINKS TO RELATED DOCUMENTS	
Dimensions	<a href="http://www.vishay.com/doc?95311">http://www.vishay.com/doc?95311</a>



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